

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
60V	13mΩ @ V _{GS} = 10V	10.3A
	18mΩ @ V _{GS} = 4.5V	8.8A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Motor control
- DC to DC converters
- Reverse polarity protection

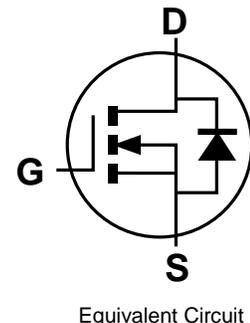
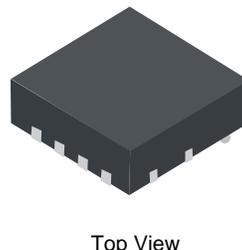
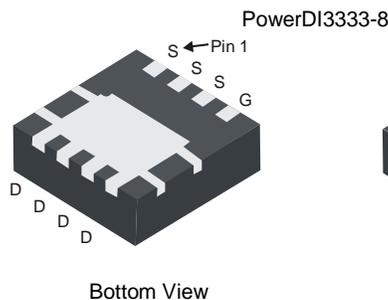
Features and Benefits

- Low R_{DS(ON)} – Ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMN6013LFGQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Package: PowerDI[®] 3333-8
- Package Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.072 grams (Approximate)



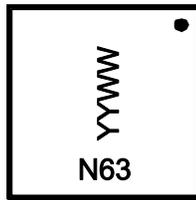
Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Quantity	Carrier
DMN6013LFGQ-7	PowerDI3333-8	2,000	Tape & Reel
DMN6013LFGQ-13	PowerDI3333-8	3,000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

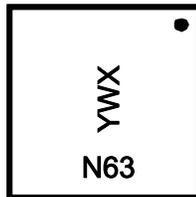
Marking Information

Site1



N63 = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 23 = 2023)
 WW = Week Code (01 to 53)

Site2:



N63 = Product Type Marking Code
 YWX = Date Code Marking
 Y = Year (ex: 3 = 2023)
 W = Week (ex: a = Week 27, z Represents Week 52 and 53)
 X = Internal Code (ex: U = Monday)

Date Code Key

Year	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	3	4	5	6	7	8	9	0	1	2	3	4
Week	1-26				27-52				53			
Code	A-Z				a-z				z			
Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat					
Code	T	U	V	W	X	Y	Z					

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	T _A = +25°C	10.3	A
	T _A = +70°C	8.3	A
	T _C = +25°C	45	A
	T _C = +100°C	28	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	58.3	A
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	3	A
Avalanche Current, L = 0.1mH	I _{AS}	33.3	A
Avalanche Energy, L = 0.1mH	E _{AS}	56.8	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	1	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	Steady State	123
		t < 10s	69
Total Power Dissipation (Note 6)	P _D	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	Steady State	60
		t < 10s	34
Total Power Dissipation (Note 6)	P _D	40	W
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	3.2	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current, T _J = +25°C	I _{DSS}	—	—	1	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1	1.8	3	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	9.3	13	mΩ	V _{GS} = 10V, I _D = 10A
		—	12.3	18		V _{GS} = 4.5V, I _D = 8A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 1.7A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	2577	—	pF	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{oss}	—	162	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	132	—	pF	
Gate Resistance	R _g	—	0.9	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	26.6	—	nC	V _{DS} = 30V, I _D = 10A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	55.4	—	nC	
Gate-Source Charge	Q _{gs}	—	9.3	—	nC	
Gate-Drain Charge	Q _{gd}	—	12.6	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	6.2	—	ns	V _{GS} = 10V, V _{DS} = 30V, R _G = 3Ω, I _D = 10A
Turn-On Rise Time	t _R	—	9.9	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	27.6	—	ns	
Turn-Off Fall Time	t _F	—	11.7	—	ns	
Body Diode Reverse Recovery Time	t _{RR}	—	9.4	—	ns	I _F = 10A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q _{RR}	—	18.6	—	nC	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

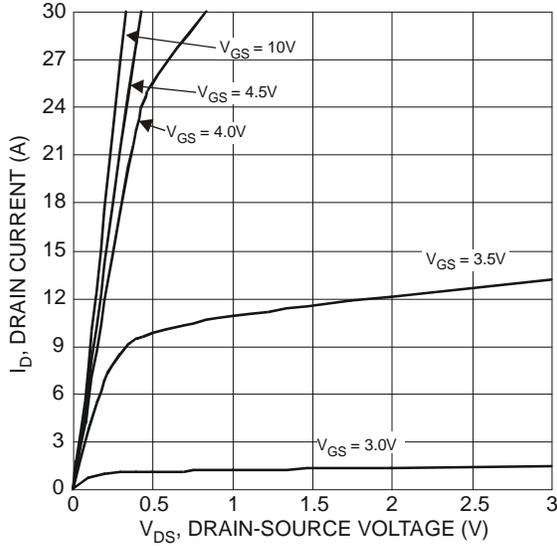


Figure 1 Typical Output Characteristics

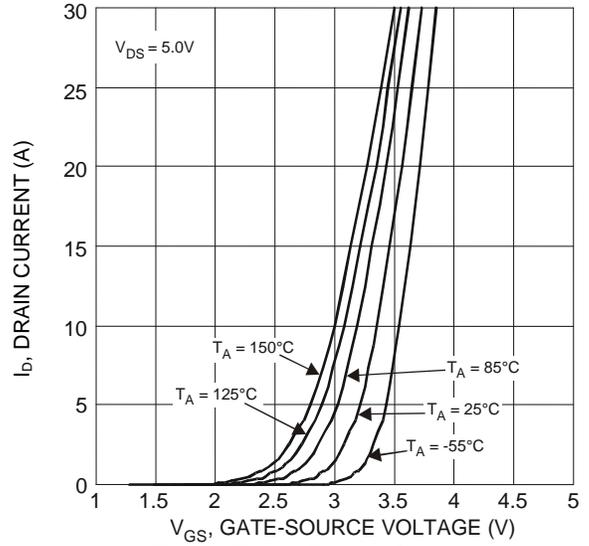


Figure 2 Typical Transfer Characteristics

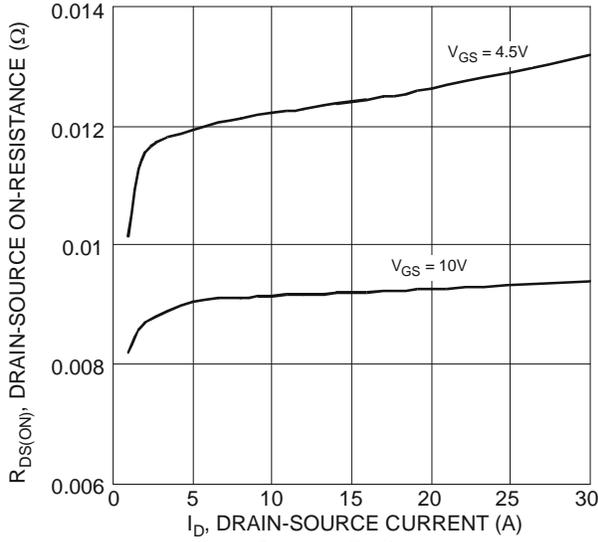


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

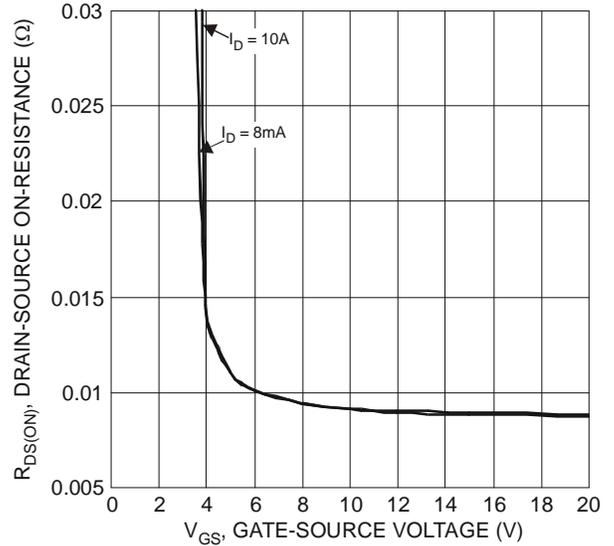


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

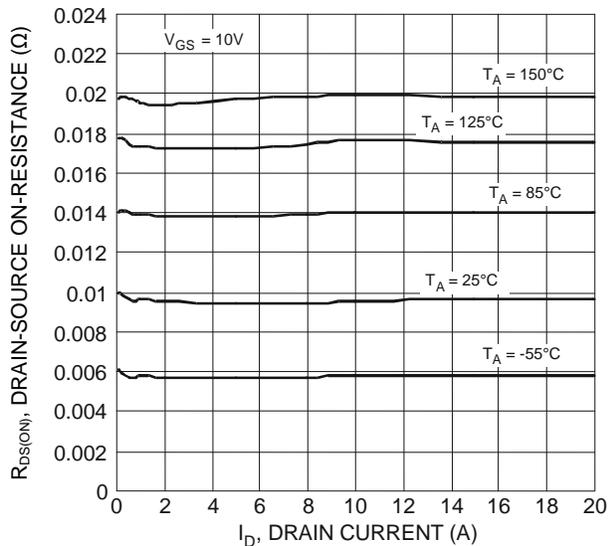


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

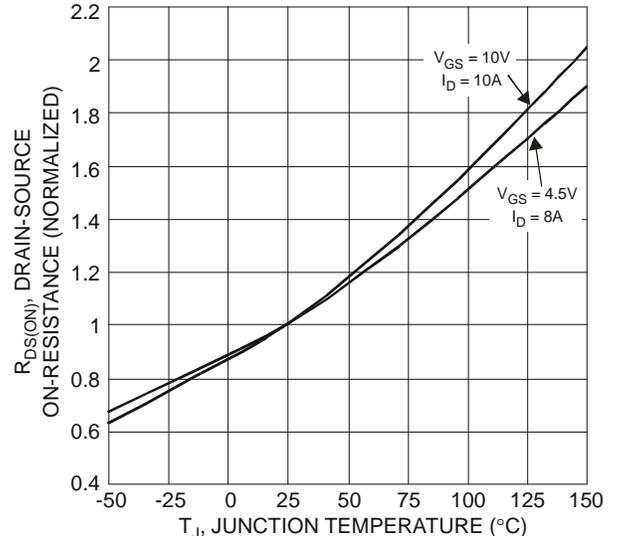


Figure 6 On-Resistance Variation with Temperature

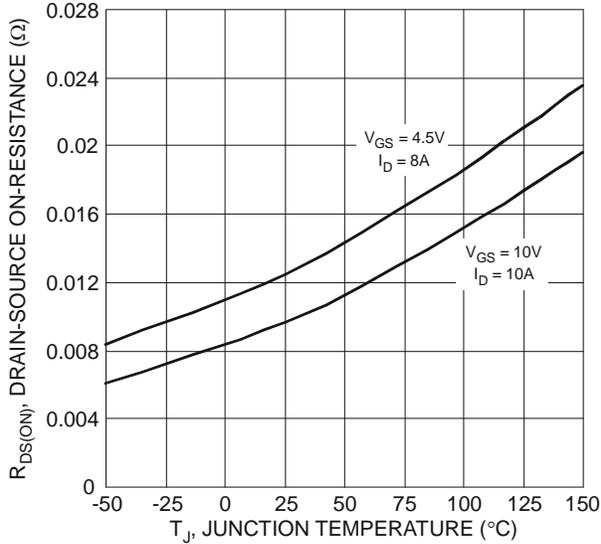


Figure 7 On-Resistance Variation with Temperature

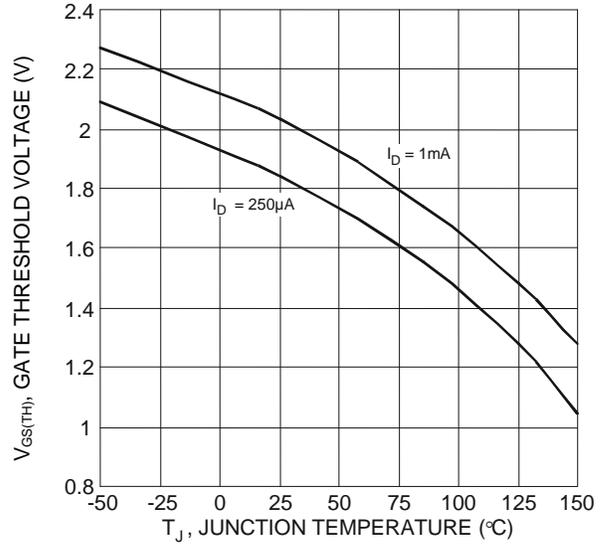


Figure 8 Gate Threshold Variation vs. Junction Temperature

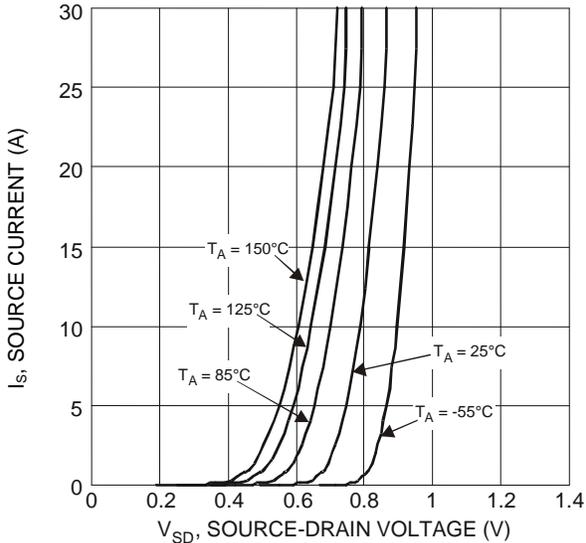


Figure 9 Diode Forward Voltage vs. Current

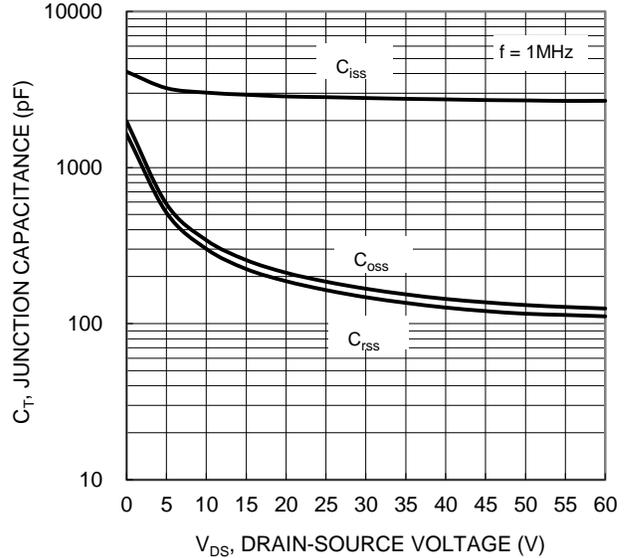


Figure 10 Typical Junction Capacitance

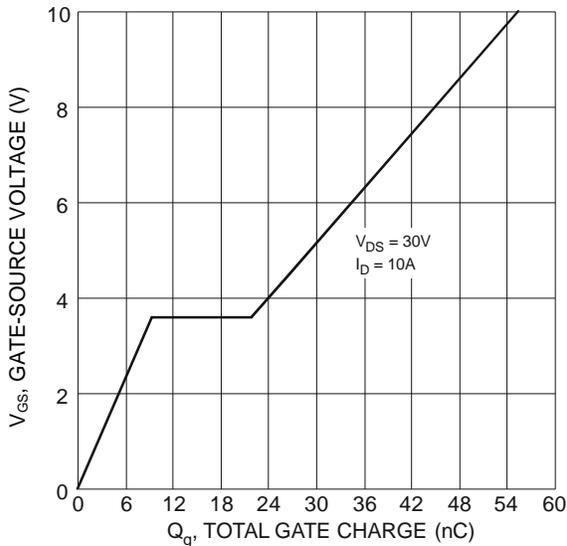


Figure 11 Gate Charge

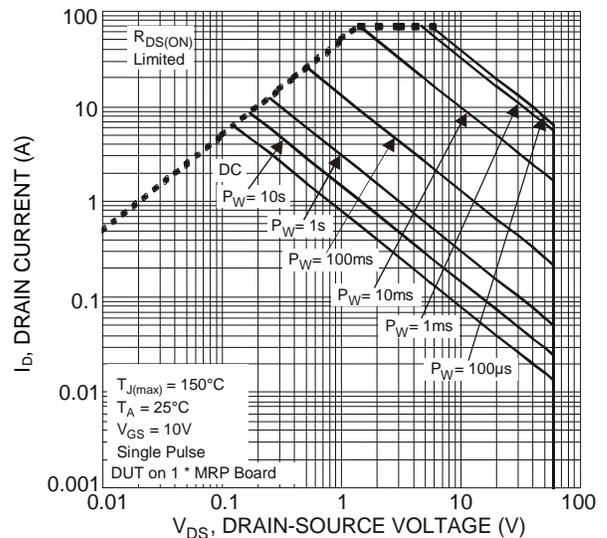
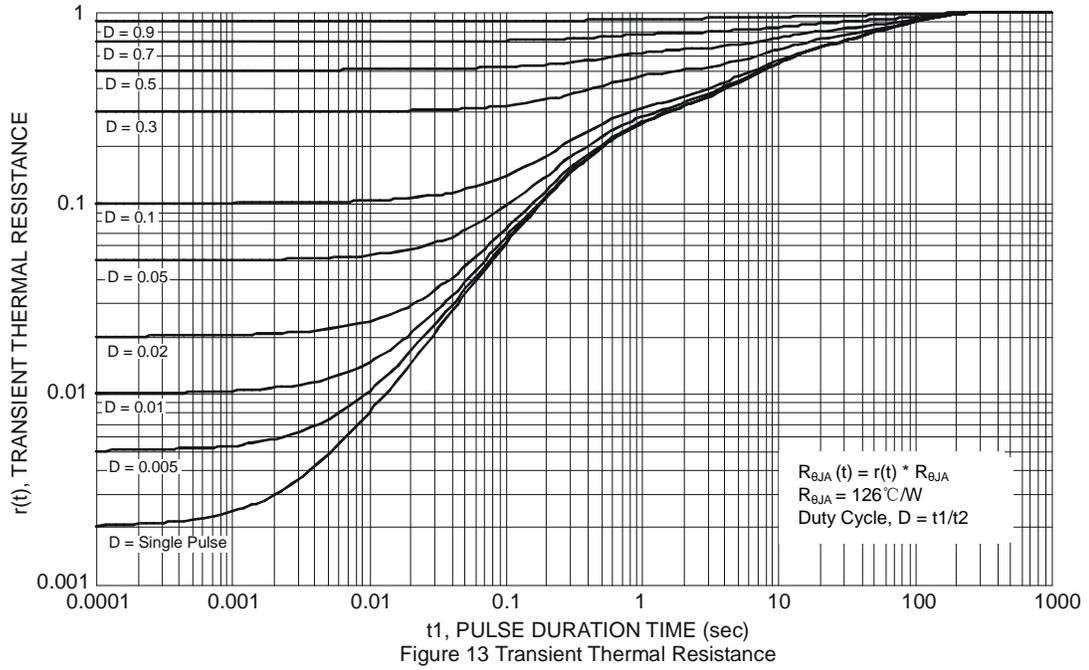


Figure 12 SOA, Safe Operation Area



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